

Zener Diode Chips for ESD Protection

1. Feature:

- 1-1 Silicon Zener diode chips for electrostatic discharge (ESD) protection application
- 1-2 This specification applies to P-Type silicon Zener diode chip Device NO:WT-Z105P-AU4

2. Structure:

- 2-1 Planar type: P/N Diode
- 2-2 Electrodes:
 - Top side:Gold Pad(Anode).
 - Back side:Gold Layer(Cathode).

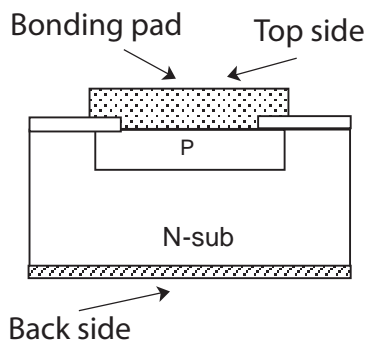
3. Size:

- 3-1.*Chip size : 5.9 mils x 5.9 mils (150 μm x 150 μm).
 - 3-2. Chip thickness : 3.3 ± 0.6 mils (85 ± 15 μm).
 - 3-3. Bonding pad : 3.54 mils x 3.54 mils (90 μm x 90 μm) .
 - 3-4. Pattern drawing : Refer to the attached drawing.
- *Including scribing line. The chip size is(125±10)²μm² after dicing.

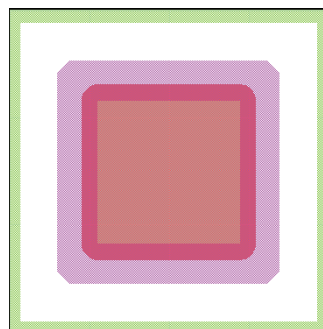
4. Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Zener Voltage	Vz	Iz=5mA	5.7	-	6.7	V
Reverse Leakage Current	IR	VR=4V	-	-	100	nA
		VR=5V	-	-	0.5	μA
Forward Voltage	Vf	If=20mA	-	-	1.2	V
Electrostatic Discharge	ESD	HBM MIL-STD883	8.0	-	-	KV

5. Drawing:



Top View



6. Protection Circuit

